

GESD0501CH

Bidirectional TVS Diode

DESCRIPTION

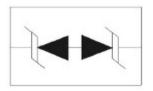
The GESD0501CH is designed for applications transient overvoltage reauirina protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, business machines, communication printers. systems, medical equipment and other applications. These devices are ideal for situations where board space is at a premium.

The GESD0501CH has been specifically designed to protect sensitive components which are connected to power, data and transmission lines from overvoltage caused by ESD(electrostatic CDE discharge), (Cable Discharge Events), and EFT (electrical fast transients).

ORDERING INFORMATION

- ♦Device: GESD0501CH
- ♦Package: DFN1006
- ♦Marking: FXC
- ♦Material: Halogen free and RoHS compliant
- ♦Packing: Tape & Reel
- ♦Quantity per reel: 10,000pcs

PIN CONFIGURATION



FEATURES

- ♦ESD per IEC 61000-4-2 ±30 kV (Contact)
- ♦ ESD per IEC 61000-4-2 ±30 kV (Air)
- ♦IEC61000-4-4 (EFT) 40A (5/50ηs)
- ♦Peak power dissipation: 675W (8/20µs)
- ♦Low clamping voltage
- ♦Working voltages : 5V
- ♦Low leakage current

MACHANICAL DATA

- ♦DFN1006 package
- ♦Flammability Rating: UL 94V-0
- ✦High temperature soldering guaranteed: 260℃/10s
- ♦Packaging: Tape and Reel
- ♦Reel size: 7 inch

APPLICATIONS

- ♦ Cell Phone Handsets and Accessories
- ♦ Microprocessor based equipment
- ♦ Personal Digital Assistants (PDA's)
- ♦Notebooks, Desktops, and Servers
- ♦Portable Instrumentation
- \diamond Networking and Telecom
- ♦ Serial and Parallel Ports
- ♦Peripherals

PACKAGE OUTLINE





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ABSOLUTE MAXIMUM RATING						
Symbol	Parameter	Value	Units			
V _{ESD}	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±30 ±30	kV			
P _{PP}	Peak Pulse Power (8/20µs)	675	W			
T _{OPT}	Operating Temperature	-55~150	°C			
T _{STG}	Storage Temperature	-55~150	℃			

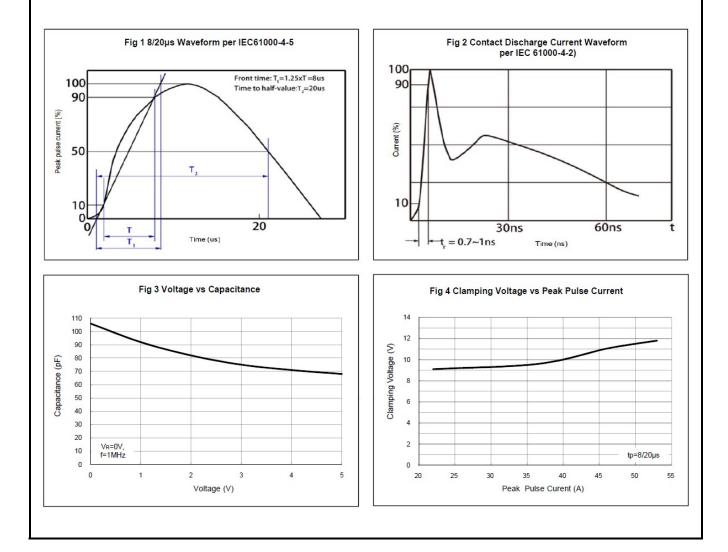
ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V _{RWM}	Reverse Working Voltage				5.0	V		
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA	5.6		9.0	V		
I _R	Reverse Leakage Current	V _{RWM} = 5V			1.0	μA		
Vc	Clamping Voltage	I_{PP} = 30A, t_p = 8/20µs		9.5	12	V		
Vc	Clamping Voltage	I _{PP} = 45A, t _p = 8/20μs		11	15	V		
CJ	Junction Capacitance	V _R = 0V, f = 1MHz		105	120	pF		



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ELECTRICAL CHARACTERISTICS CURVE







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DFN1006 PACKAGE OUTLINE DIMENSIONS

